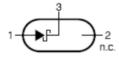


#### **Features**

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- ◆ High Conductance
- For General Purpose Switching Applications





# Absolute Maximum Ratings Ta = 25°C

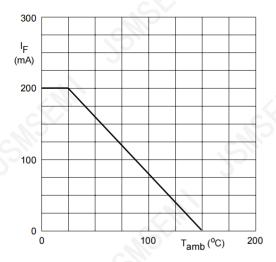
Parameter	Symbol	Rating	Unit
Reverse Voltage	VR	250	V
Forward Current	lF	200	mA
Power Dissipation	PD	200	mW
Operating Junction Temperature Range	TJ	-55 to +150	$^{\circ}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}$

### Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Тур	Max	Unit	
Reverse Breakdown Voltage	V(BR)	IR=100 μ A	250			V	
Forward Voltage		IF=100mA			1.0		
	VF	IF=200mA	, C3V	1	1.25	V	
Reverse Leakage	lR	VR=200V			100	nA	
Junction Capacitance	Cj	VR=0V, f=1.0MHz	9		5.0	pF	
Reverse Recover Time	Trr				50	nS	

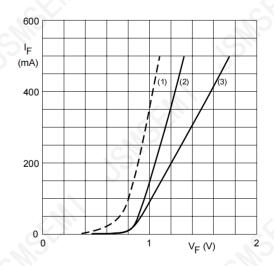


### Typical Characterisitics



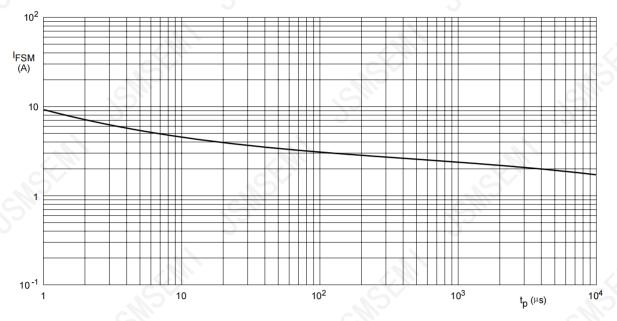
Device mounted on an FR4 printed-circuit board.

Fig.1 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) T<sub>j</sub> = 150 °C; typical values.
- (2) T<sub>i</sub> = 25 °C; typical values.
- (3) T<sub>j</sub> = 25 °C; maximum values.

Fig.2 Forward current as a function of forward voltage.

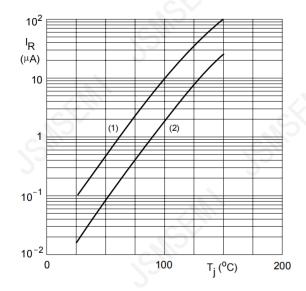


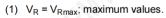
Based on square wave currents.

T<sub>j</sub> = 25 °C prior to surge.

Fig.3 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

### Typical Characterisitics





<sup>(2)</sup>  $V_R = V_{Rmax}$ ; typical values.

Fig.5 Reverse current as a function of junction temperature.

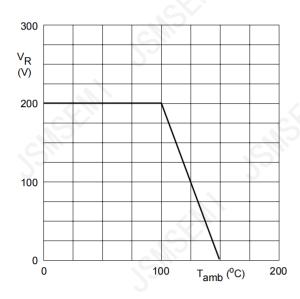
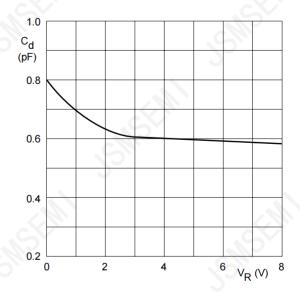


Fig.7 Maximum permissible continuous reverse voltage as a function of the ambient temperature.



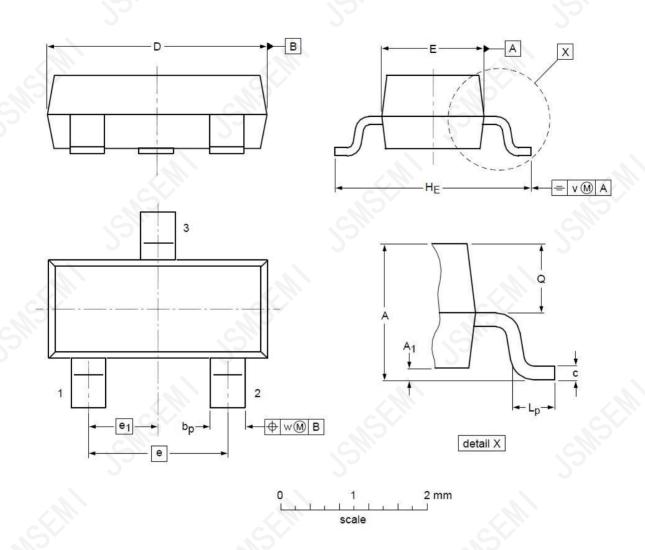
f = 1 MHz;  $T_j = 25 °C$ .

Fig.6 Diode capacitance as a function of reverse voltage; typical values.



# **Package Information**

SOT-23-3



#### **DIMENSIONS** ( unit : mm )

Symbol	Min	Тур	Max	Symbol	Min	Тур	Max
Α	0.90	1.01	1.15	A <sub>1</sub>	0.01	0.05	0.10
b <sub>p</sub>	0.30	0.42	0.50	С	0.08	0.13	0.15
D	2.80	2.92	3.00	) E	1.20	1.33	1.40
е		1.90		e <sub>1</sub>		0.95	
HE	2.25	2.40	2.55	Lp	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	(0	0.20	
w		0.10			.cll		



## **Revision History**

Rev.	Change	Date
V1.0	Initial version	2/23/2024

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